Silicon Carbide Schottky Diode

Features

Positive temperature coefficient Temperature-independent switching Maximum working temperature at 175 °C Unipolar devices and zero reverse recovery current Zero forward recovery current Essentially no switching losses Reduction of heat sink requirements High-frequency operation Reduction of EMI

Typical Applications

Typical applications are in power factor correction(PFC), solar inverter, uninterruptible power supply, motor drives, photovoltaic inverter, electric car and charger.

Mechanical Data

Package: TO-247AC Terminals: Tin plated leads Polarity: As marked

Maximum Ratings (T_c=25 Unless otherwise specified

PARAMTETER	SYMBOL	UNIT	VALUE
Device marking code			D112015NGG2
Reverse voltage (repetitive peak) @ T _j =25°C	V _{RRM}	V	1200
Reverse voltage (Surge Peak) @ T _j =25°C	V _{RSM}	V	1200
Reverse voltage (DC) @ T _j =25°C	V _{DC}	V	1200
Continuous forward current @ T _c =25°C T _c =135°C T _c =160°C	lF	A	70 33 15
Non-repetitive peak forward surge current @ T _c =25°C, tp=10ms, Half Sine Wave	I _{F6M}	А	144
Power Dissipation@ T _c =25°C T _c =110°C	Ртот	W	319 13 8
i²t VaFue@ Tc=25°C ftp=10ms	i ² dt	A ² S	103
Operating junction an& Storage temperature range	T _j ,T _{stg}	°C	655 to +175

Electrical Characteristics

PARAMTETER	SYMBOL	UNIT	TEST CONDITIONS	Тур.	Max.
Forward voltage drop	VF	V	I _F =15A, T _j =25°C	1.25	1.45
			I _F =15A, T _j =175°C	1.65	1.85
Poverse leakage current	I _R	μA	V _R =1200V, T _j =25°C	0.5	25
Reverse leakage current			V _R =1200V, T _j =175°C	5	-
Total capacitive charge	Qc	nC	$V_R=800V, T_j=25^{\circ}C, QC=_0^{VR}C(V)dV$	114	
	С	pF	V _R =0V, f=1MHZ	1552	-
Total capacitance			V _R =400V, f=1MHZ	107	-
			V _R =800V, f=1MHZ	79	-
Capacitance Stored Energy	Ec	μJ	V _R =800V	29.3	-

Thermal Characteristics Ta=25 U

Ta=25 Unless otherwise specified

PARAMETER	SYMBOL	UNIT	VALUE
Thermal resistance	R _{J-C}	°C/W	0.47

Characteristics (Typical)

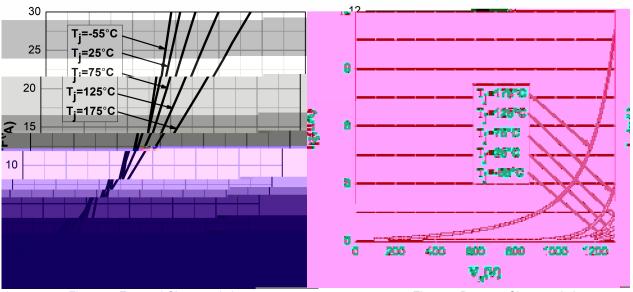


Figure 1. Forward Characteristics

Figure2. Reverse Characteristic

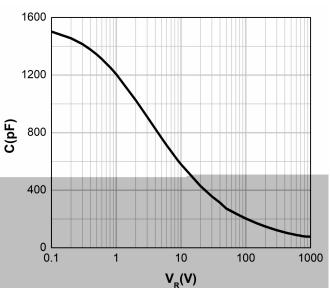


Figure 3. Capacitance vs. Reverse Voltage

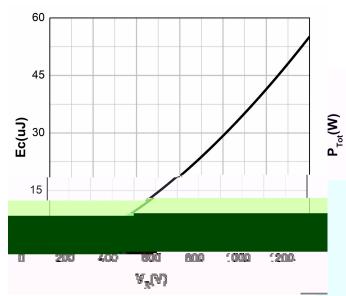
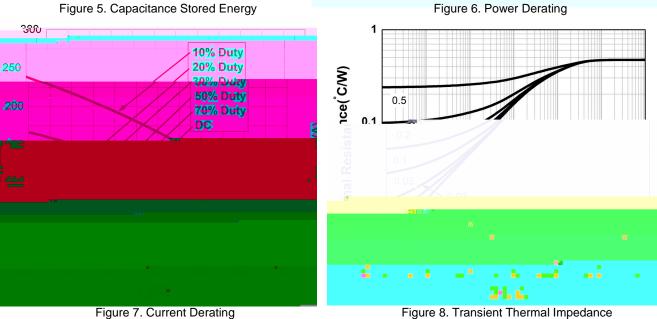


Figure 5. Capacitance Stored Energy



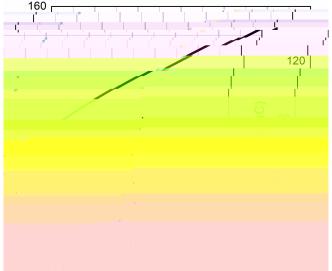
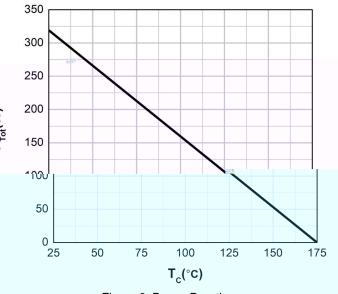


Figure 4. Total Capacitance Charge vs. Reverse Voltage



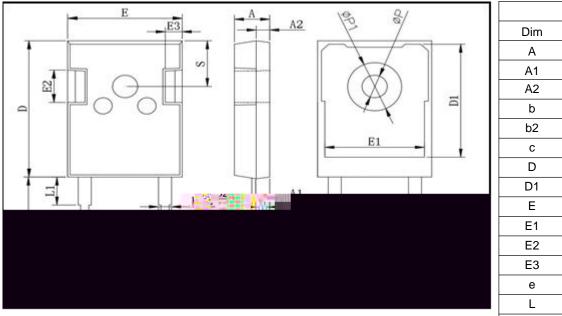
3/5







Outline Dimensions



Dim	Min	Max	
А	4.80	5.20	
A1	2.21	2.61	
A2	1.85	2.15	
b	1.00	1.40	
b2	1.91	2.21	
С	0.50	0.70	
D	20.70	21.30	
D1	16.25	16.85	
E	15.50	16.10	
E1	13.00	13.60	
E2	4.80	5.20	
E3	2.30	2.70	
е	10.88 TYP		
L	19.62	20.22	
L1	-	4.30	
Р	3.40	3.80	
P1	-	7.30	
S	6.15 TYP		

TO-247-2L





Disclaimer

The information presented in this document is for reference only. Yangzhou Yangjie Electronic Technology Co., Ltd. reserves the right to make changes without notice for the specification of the products displayed herein to improve reliability, function or design or otherwise.

The product listed herein is designed to be used with ordinary electronic equipment or devices, and not designed to be used with equipment or devices which require high level of reliability and the malfunction of with would directly endanger human life (such as medical instruments, transportation equipment, aerospace machinery, nuclear-reactor controllers, fuel controllers and other safety devices), Yangjie or anyone on its behalf, assumes no responsibility or liability for any damages resulting from such improper use of sale.

This publication supersedes & replaces all information previously supplied. For additional information, please visit our website http:// www.frxelec.com, or consult your nearest Yangjie's sales office for further assistance.